



PATENT ABSTRACTS OF JAPAN

(11) Publication number: **11163403 A**(43) Date of publication of application: **18.06.99**

(51) Int. Cl.

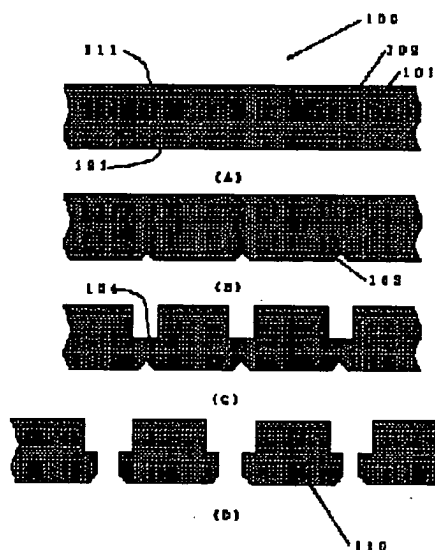
H01L 33/00
H01L 21/301(21) Application number: **09328665**(22) Date of filing: **28.11.97**(71) Applicant: **NICHIA CHEM IND LTD**(72) Inventor: **SHONO HIROBUMI**
TOYODA TATSUNORI**(54) MANUFACTURE OF NITRIDE SEMICONDUCTOR ELEMENT****(57) Abstract**

PROBLEM TO BE SOLVED: To especially provide a method for manufacturing a nitride semiconductor element which enables separation of a nitride semiconductor element formed on a substrate with high yield, related to a method for manufacturing a light-emitting diode or a laser diode capable of emitting ultraviolet to orange lights and furthermore a group III-V semiconductor element that can be driven at high temperatures.

SOLUTION: A method for manufacturing a nitride semiconductor element 110, in which a semiconductor wafer 100 having a nitride semiconductor 102 formed on a substrate 101 is divided into nitride semiconductor elements 110, and in particular includes a step of radiating a laser beam through a semiconductor wafer 100 from the side of a first main surface (111) of the semiconductor wafer 100 and/or the side of a second main surface (121) of the semiconductor wafer 100, thus forming a scribe line 103 at a focal point formed at least on the side of the second main surface 121 of the substrate 101 and/or the side of the first main surface

(111) of the substrate 101, and a step of separating the semiconductor wafer along the scribe line.


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MANUFACTURE OF NITRIDE SEMICONDUCTOR ELEMENT

Patent number: JP11163403
Publication date: 1999-06-18
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Classification:
- **International:** H01L33/00; H01L21/301
- **European:**
Application number: JP19970328665 19971128
Priority number(s):

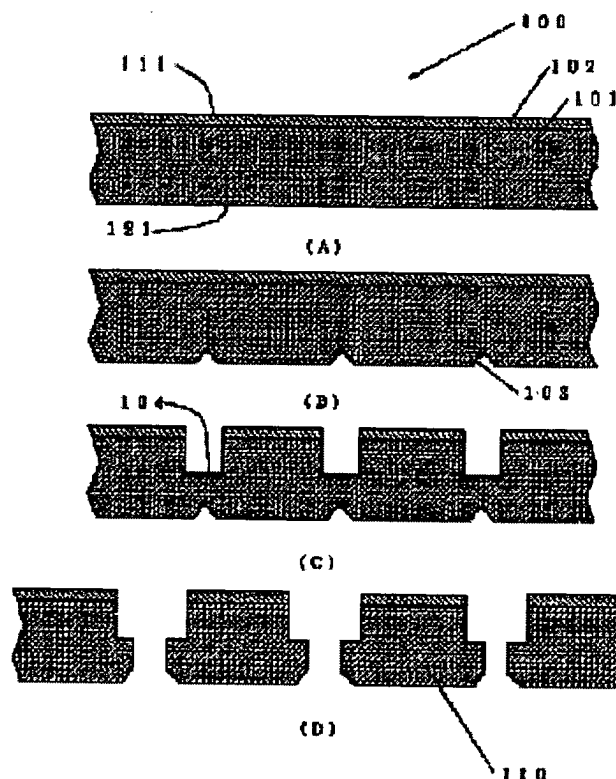
Also published as:

 JP11163403 (A)

Abstract of JP11163403

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